

accompanying pages separate from this amendment in accordance with 37 CFR § 1.121(b)(1)(iii).

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Another concern is selectivity in the etch relative to the typical overlying photoresist masking layer used to form the pattern in underlying layers. For example, certain etching chemistries utilized to etch underlying layers can provide less than desired selectivity to the photoresist layer itself. In some instances, the removal rate of the photoresist can be so great as to require undesired thicker layers of photoresist to assure that the mask pattern formed in the photoresist remains for the complete etch of the underlying layer(s). In other instances, reduced or less than desired selectivity in using certain etching chemistries can cause a reduction in the anisotropy of the etch or otherwise rounding and widening of the pattern openings themselves. This can result in less than a desired accurate transfer of the mask pattern to the underlying layer(s). Accordingly, there is a continuing effort to improve etching chemistries that increase selectivity to photoresist in the etching of underlying layers, particularly where the underlying layers include silicon nitride.
